

a second gate electrode provided on said second element formation region facing said first gate electrode and containing an impurity of the second conductivity type;

a first impurity storage region containing said first conductivity type impurity having one end connected to an end of said first gate electrode, and arranged in a direction different from the direction of arrangement of said first and second gate electrodes; and

a second impurity storage region, physically connected to said first impurity storage region by a semiconductor layer, said second impurity storage region containing said second conductivity type impurity, and having one end connected to an end of said second gate electrode, having the other end electrically connected to the other end of said first impurity storage region, and arranged in a direction different from the direction of arrangement of said first and second gate electrodes.

Please cancel claim 2 without prejudice.

Attached hereto is a marked up version of the proposed changes made to the claims by the current amendment. The attachment is captioned **“Version with Markings to Show Changes Made.”**

REMARKS

Applicant claims an improved semiconductor device having two element formation regions (4, 5) separated by an element isolation region (7). The device employs a pair of gate electrodes (2, 3) containing impurities of opposite conductivity types. Connected to the first and second gate electrodes are a pair of impurity storage regions (6, 8) arranged in a direction different from the direction of the arrangement of the gate electrodes. As amended, Applicant claims those embodiments, originally recited in claim 2, where the first and second impurity storage regions are physically connected to each other by a semiconductor layer (10). Claim 5 recites those embodiments where the first and second gate electrodes and the first and second impurity storage regions are formed in the same conductive semiconductor layer.